



# Progetto Gr. V TN HYDE - 2014

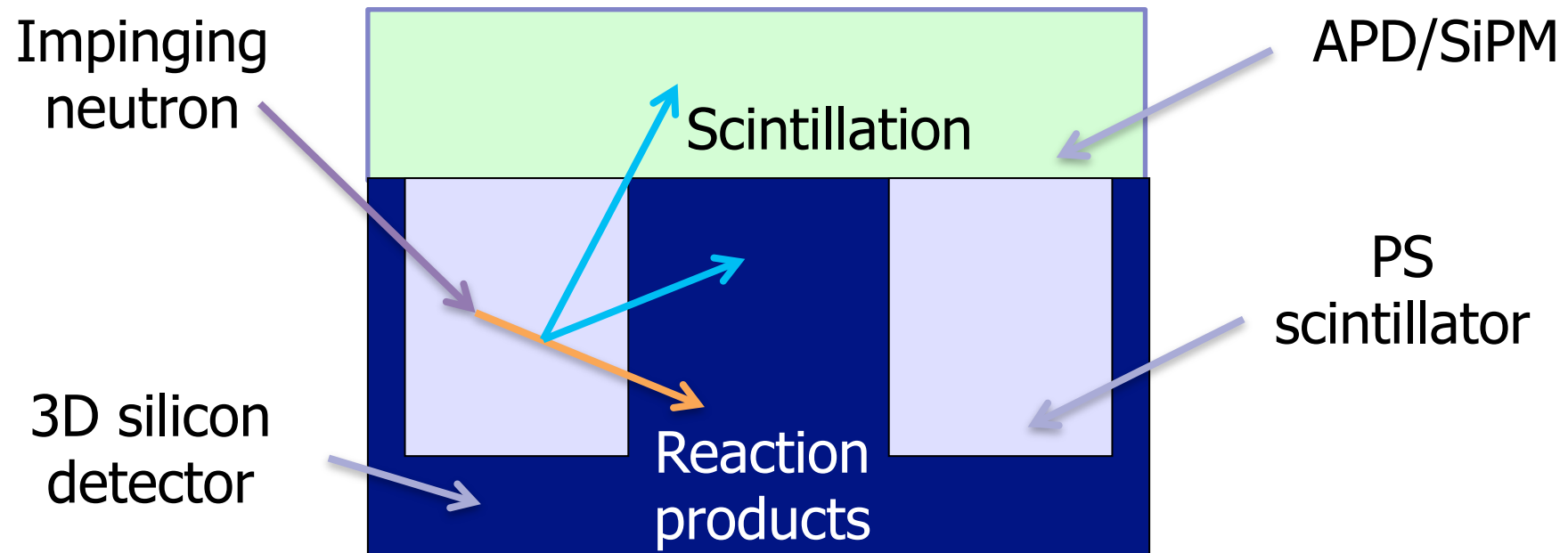
Gian-Franco Dalla Betta

Dipartimento di Ingegneria Industriale, Università di Trento

INFN Padova, Gruppo Collegato di Trento

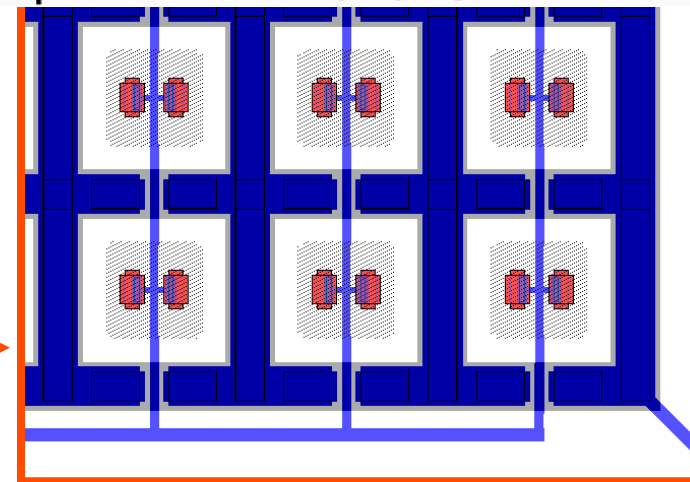
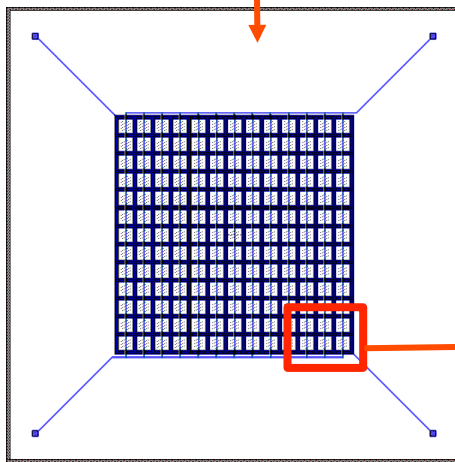
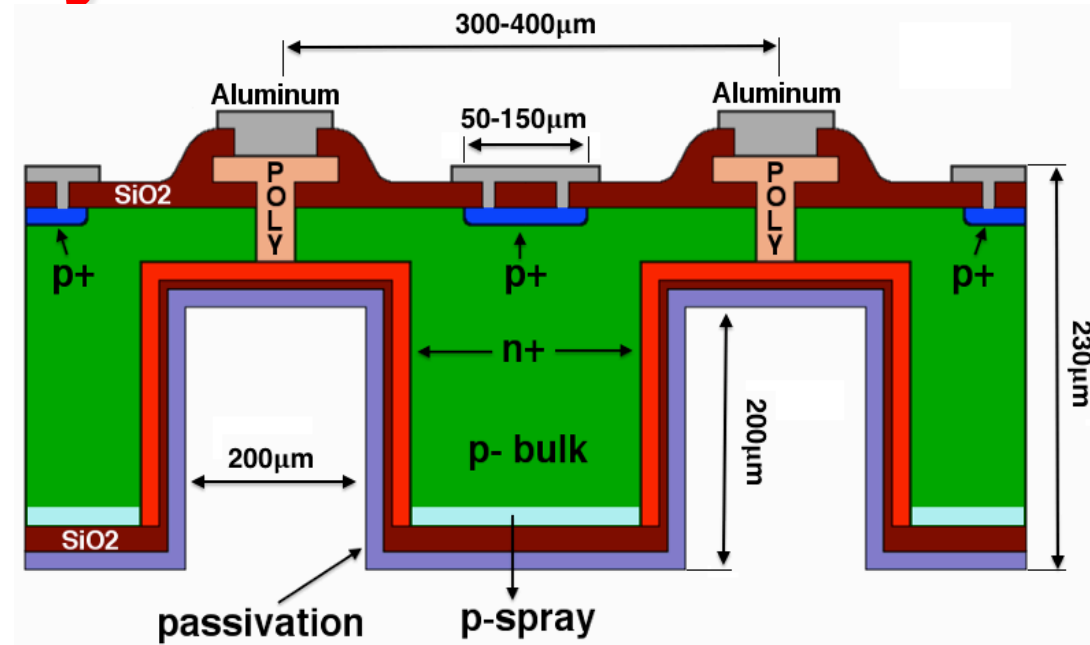
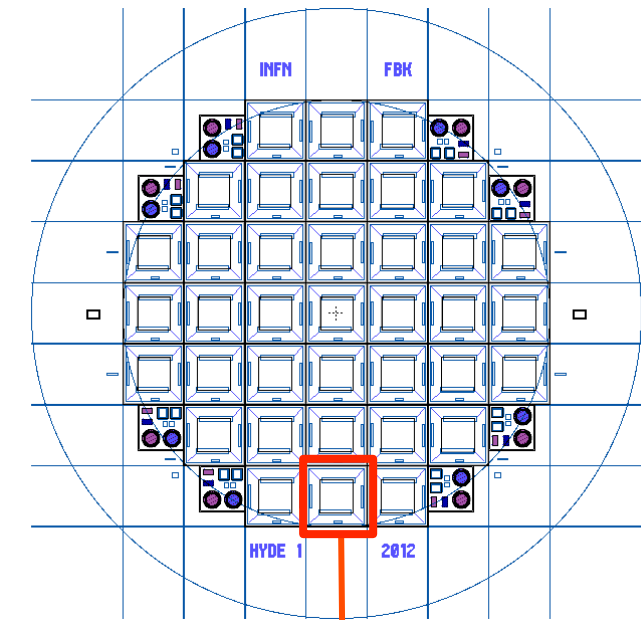
Tel.: 0461283904, e-mail: [gianfranco.dallabetta@unitn.it](mailto:gianfranco.dallabetta@unitn.it)

## HYDE: New hybrid detectors for neutrons



- ➡ Hybrid detectors obtained by pouring polysiloxane scintillators (from ORIONE) into 3D silicon detector cavities (from TRIDEAS)
- ➡ Increase of the active interaction volume for neutron, giving higher detection efficiencies.
- ➡ Reaction products detected in 3D silicon sensors, coupling to a multiplication photodetector for the detection of the scintillation light.

# Wafer layout HYDE-1

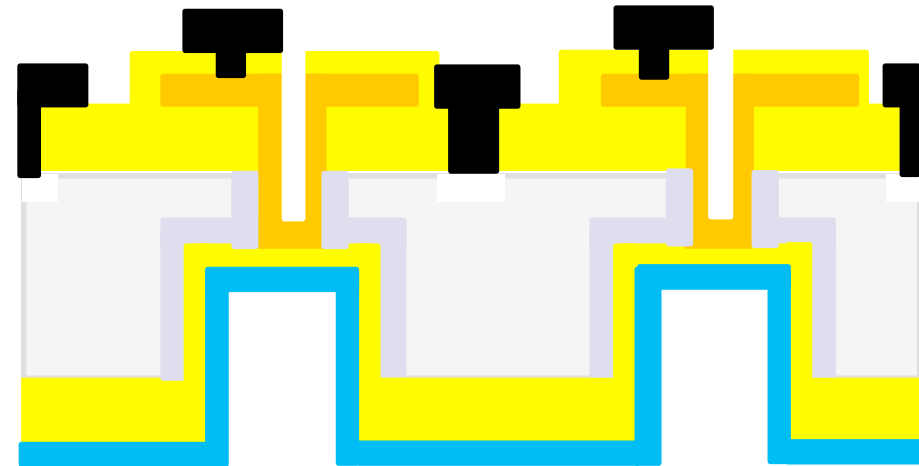


# Fabrication process @ FBK

Option A: n diffusion



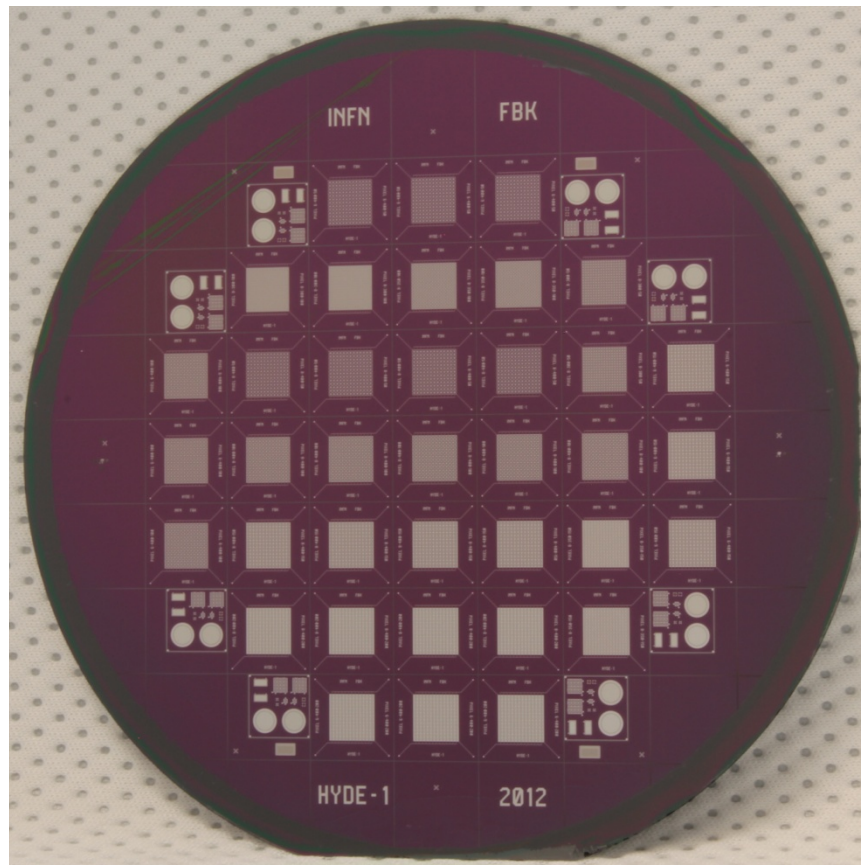
Option B: poly + n diffusion



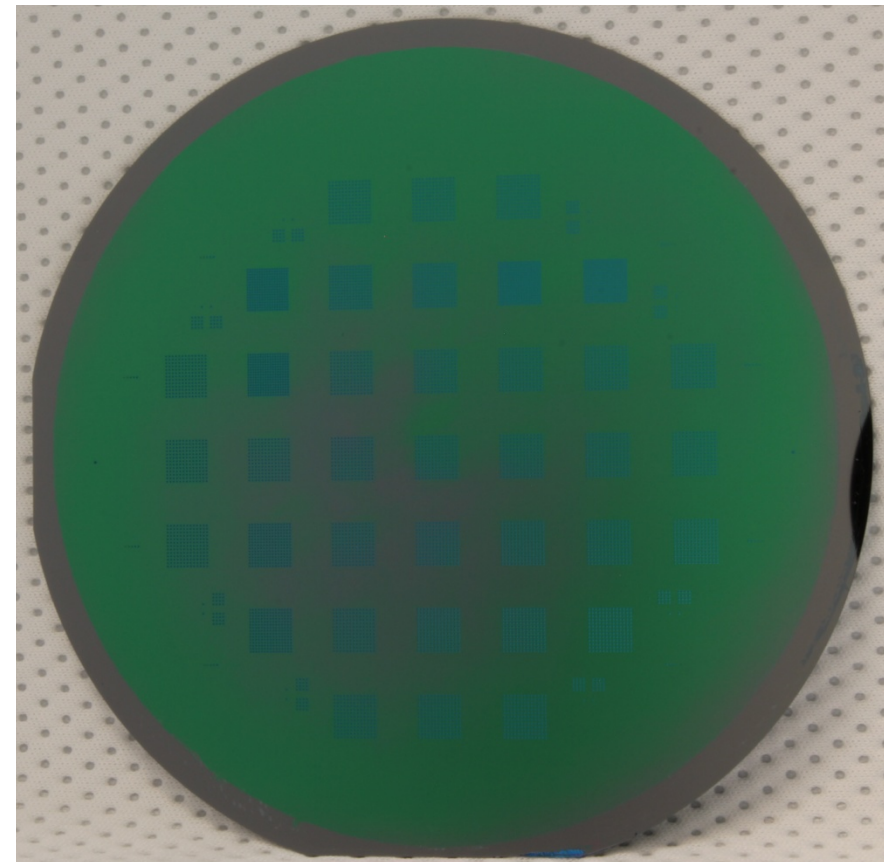
- ➔ p-type FZ wafers, 230  $\mu\text{m}$  thick:
  - ➔ isolation by p-spray on back side
  - ➔ p-plus bulk contact on front side
- ➔ 2 DRIE processes: cavities (200  $\mu\text{m}$ ) and feed-through vias (30  $\mu\text{m}$ )
- ➔ P-doping by diffusion from solid source
- ➔ Splitting on feed-through vias: n-diffusion or n-doped poly-Si

# Processed wafer

Front (all contacts)

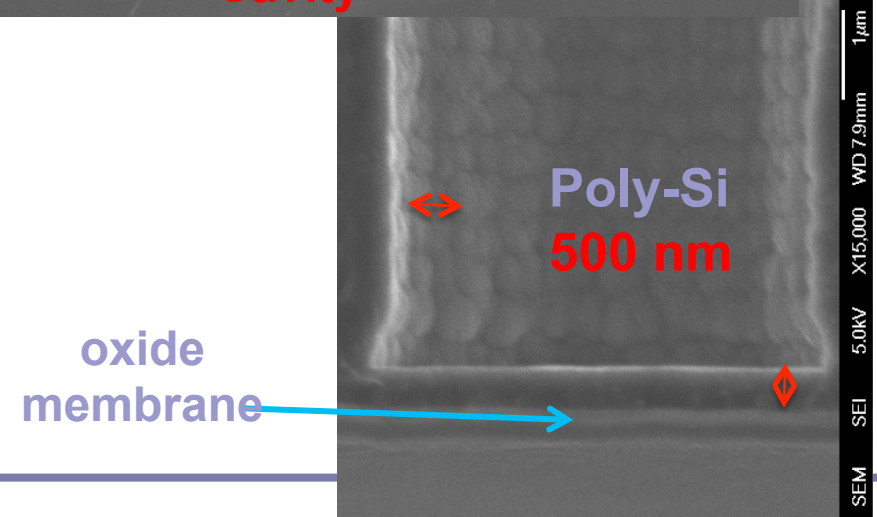
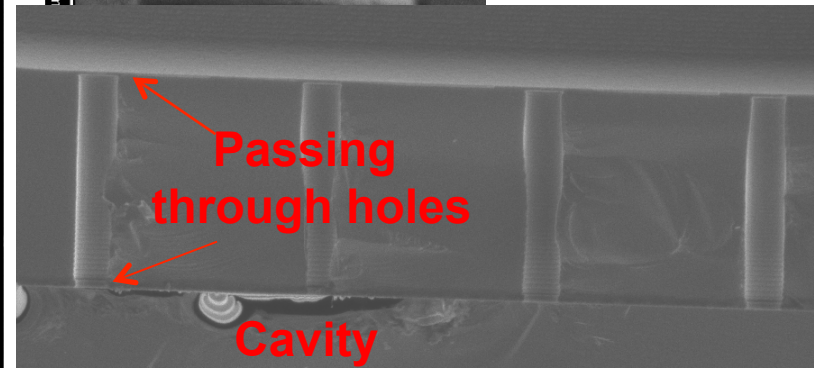
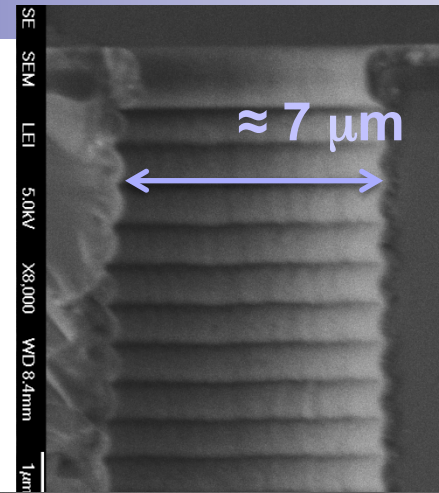
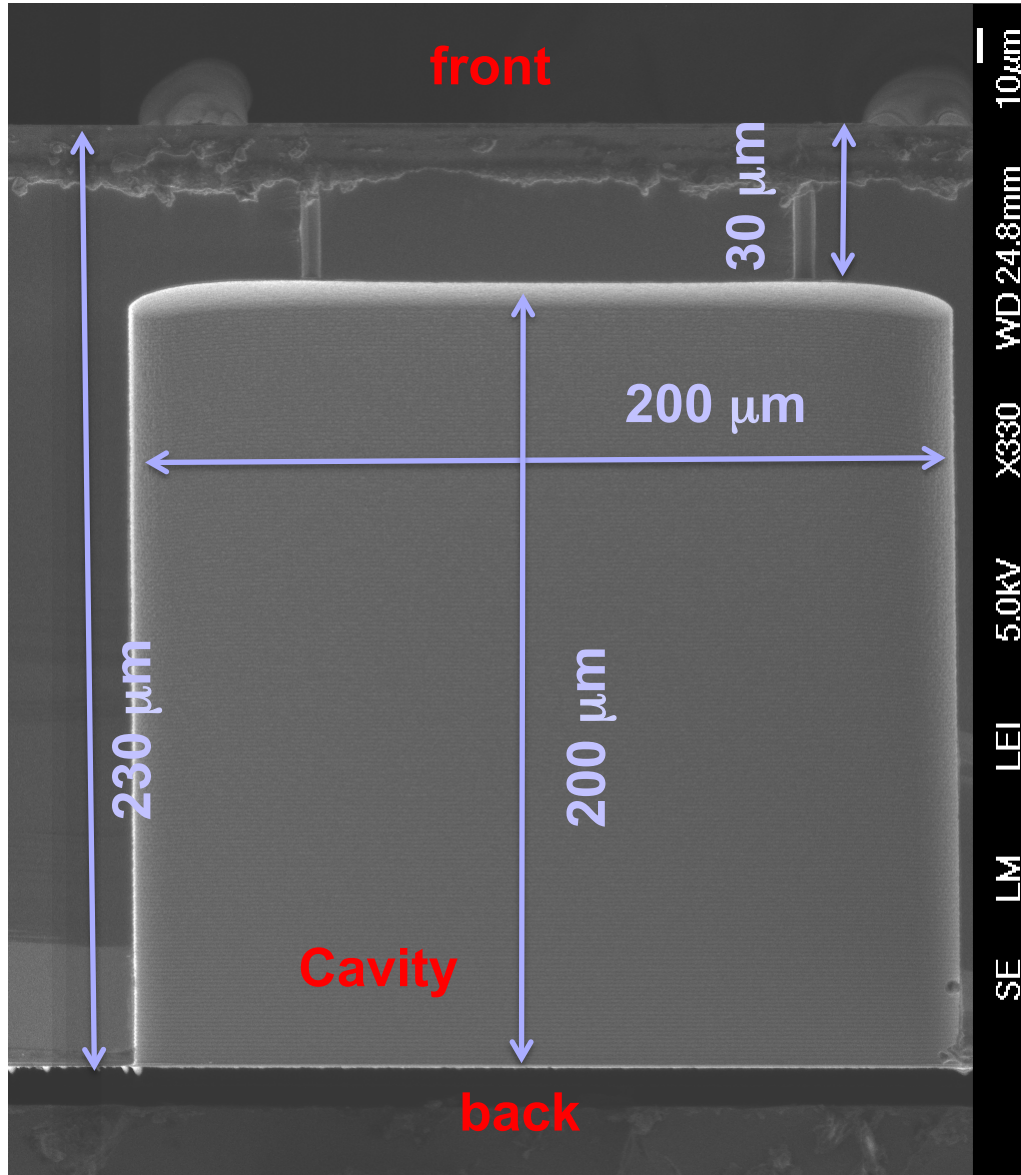


Back (only cavities)



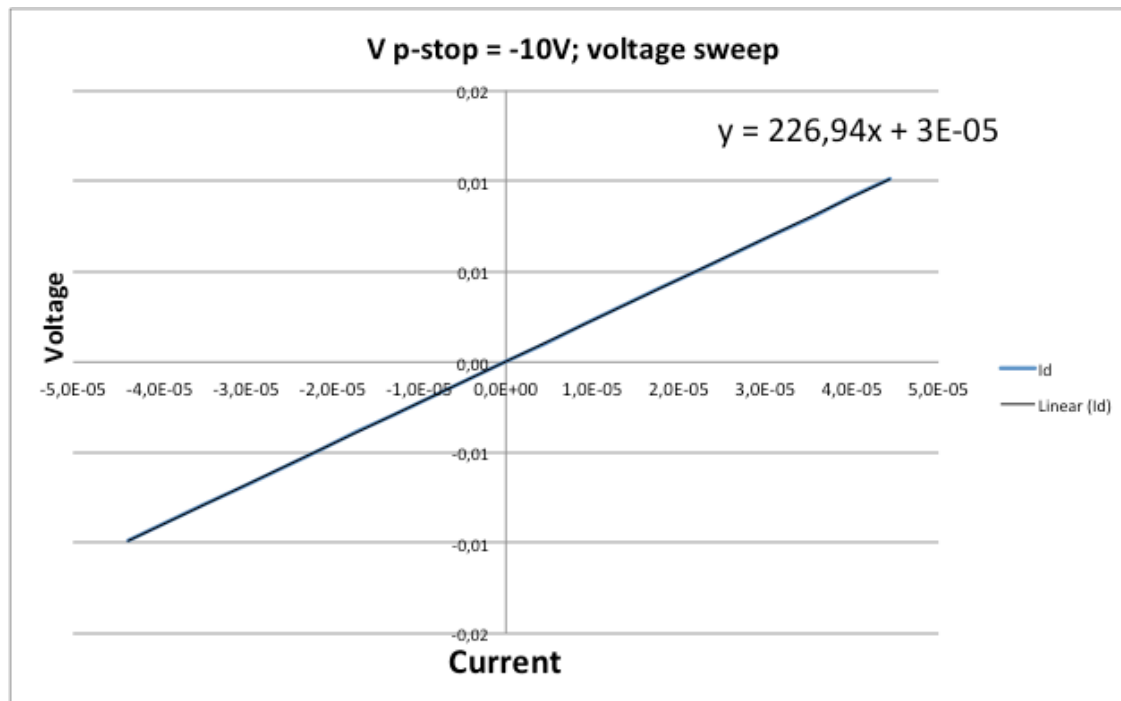


# Cross-sections at SEM

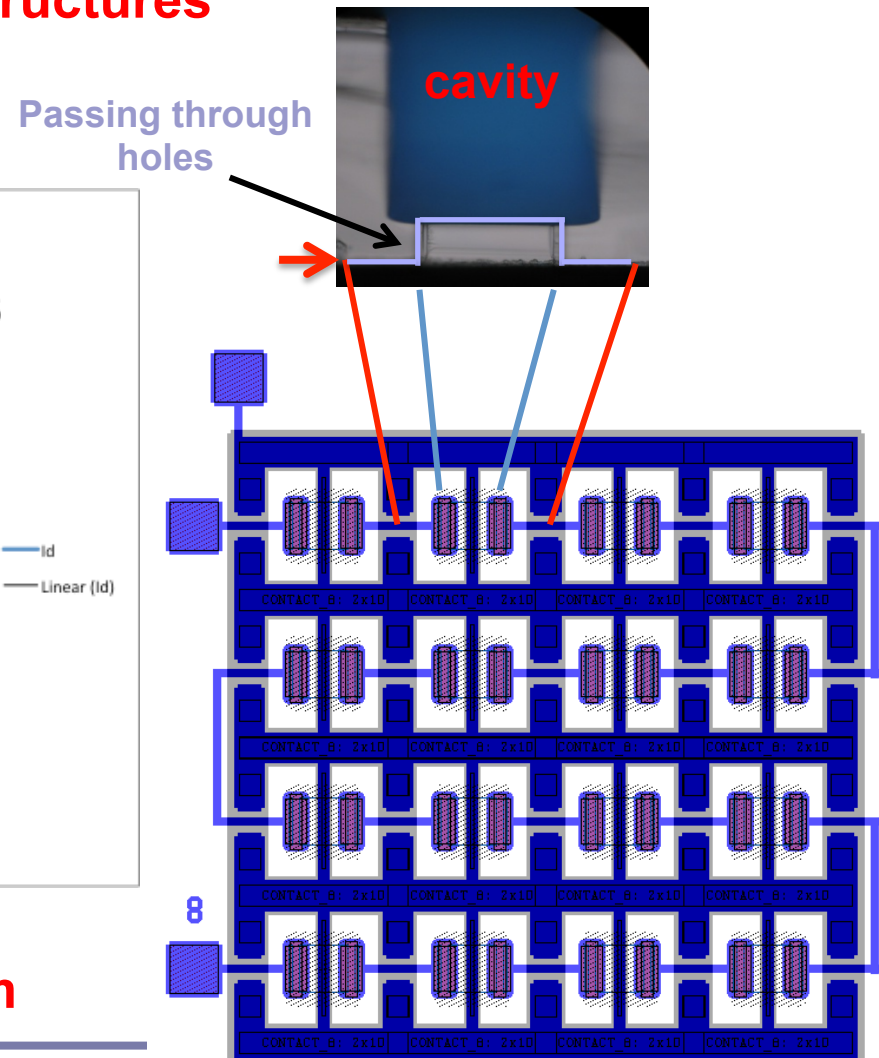


# Via holes tests

## Back/front contact checking on test structures



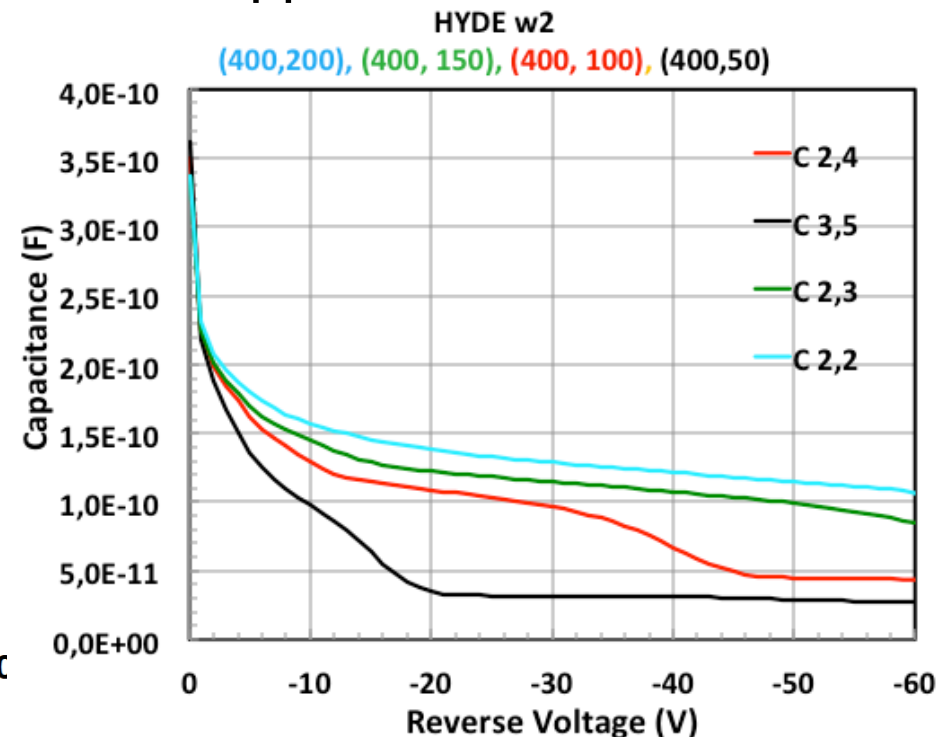
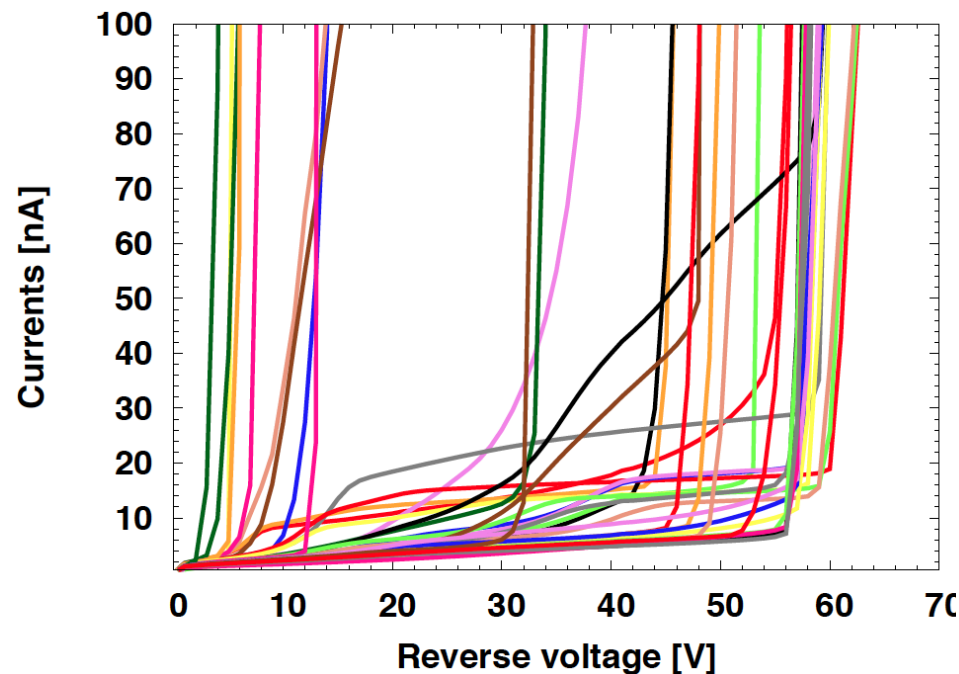
**Total resistance ~ 200 Ohm**



## Wafer 2: with poly

### Electrical test on pixel dies with different geometries

- ➔ From I-V: leakage current of a few nA/cm<sup>2</sup> and breakdown voltage of 50-60V (lower values due to defects).
- ➔ From C-V: two-phase depletion mechanism: rapid decrease due to lateral depletion, slower decrease of the other regions, with trend compatible with the different geometries of pplus.

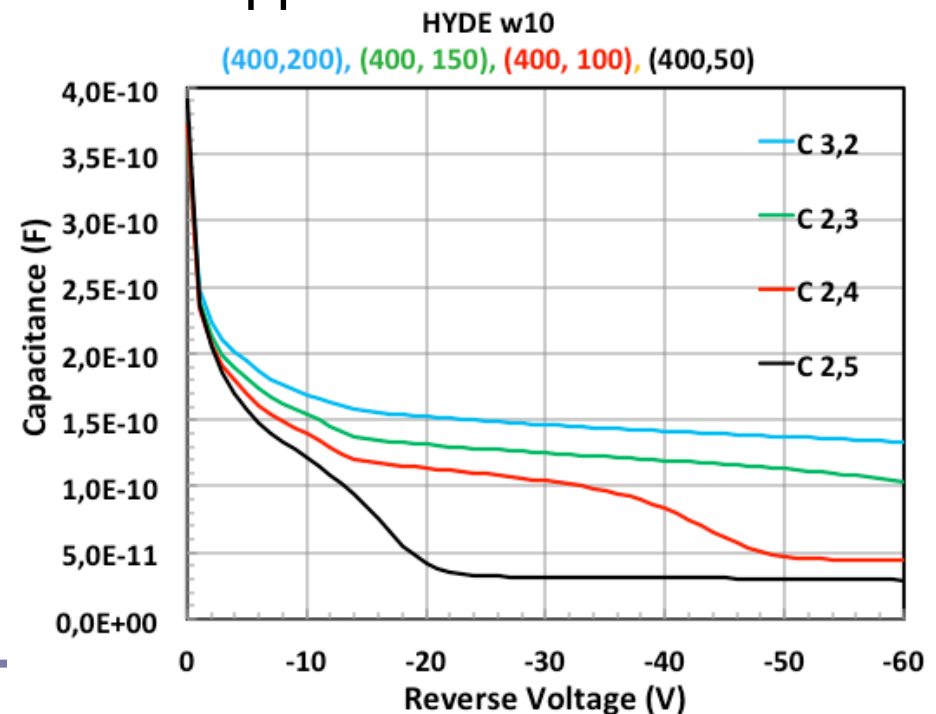
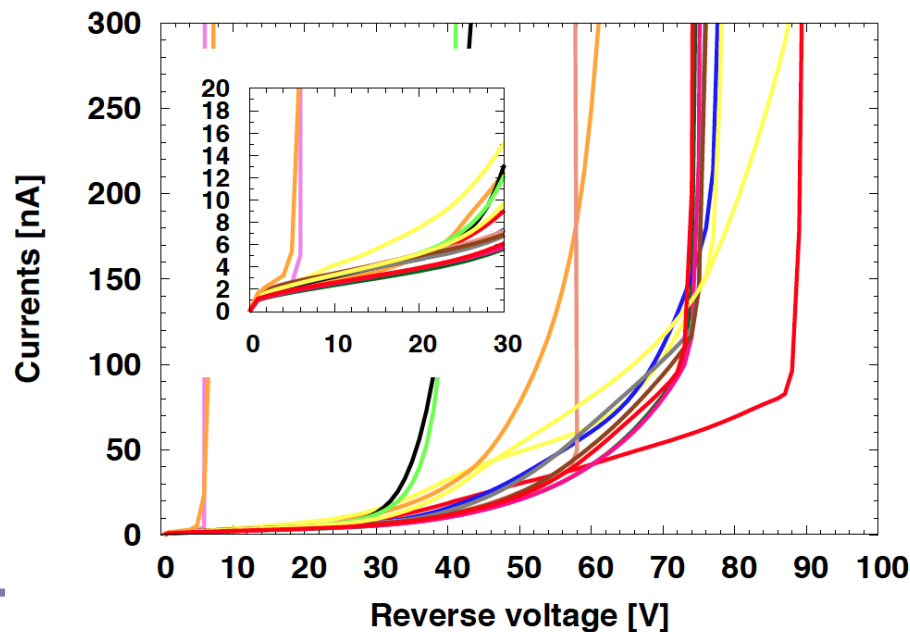




# Wafer 10: without poly

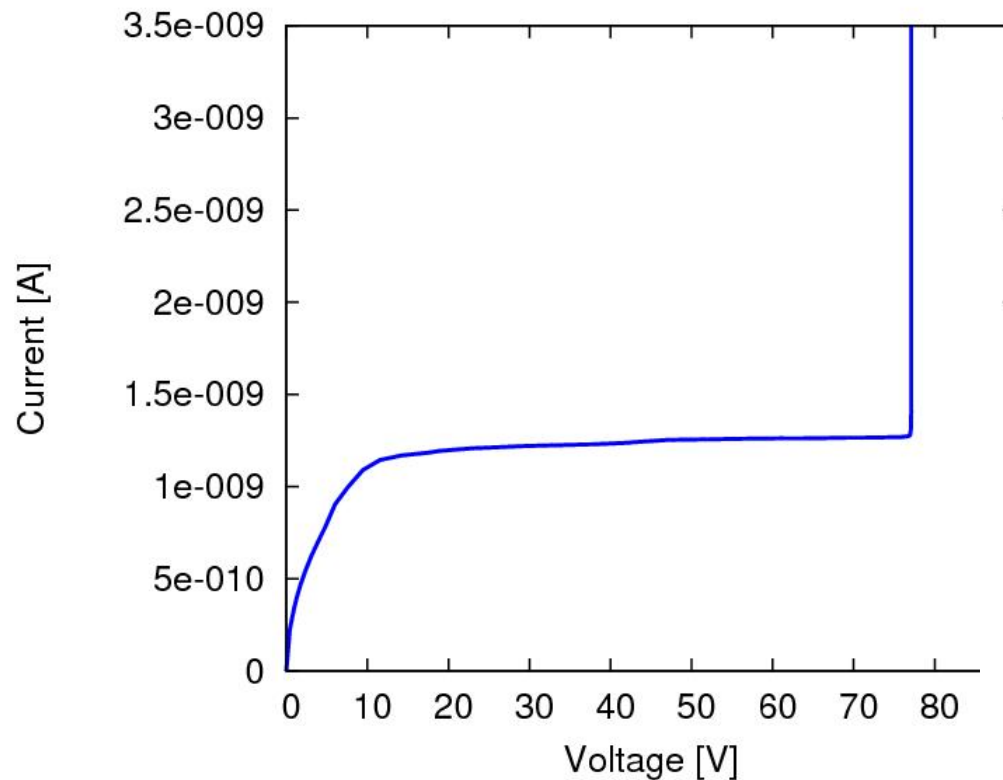
## Electrical test on pixel dies with different geometries

- ➔ From I-V: leakage current of a few nA/cm<sup>2</sup> and breakdown voltage of 70-90V (lower values due to defects).
- ➔ From C-V: two-phase depletion mechanism: rapid decrease due to lateral depletion, slower decrease of the other regions, with trend compatible with the different geometries of pplus.

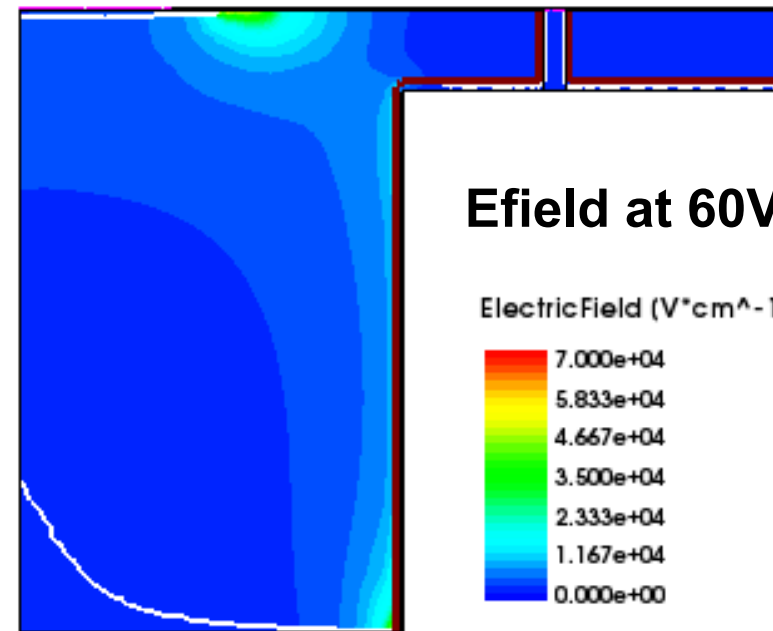
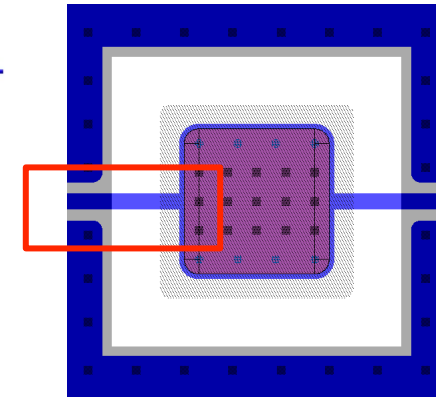


# TCAD simulation: I-V curves

## Simulated IV



400-100-d8

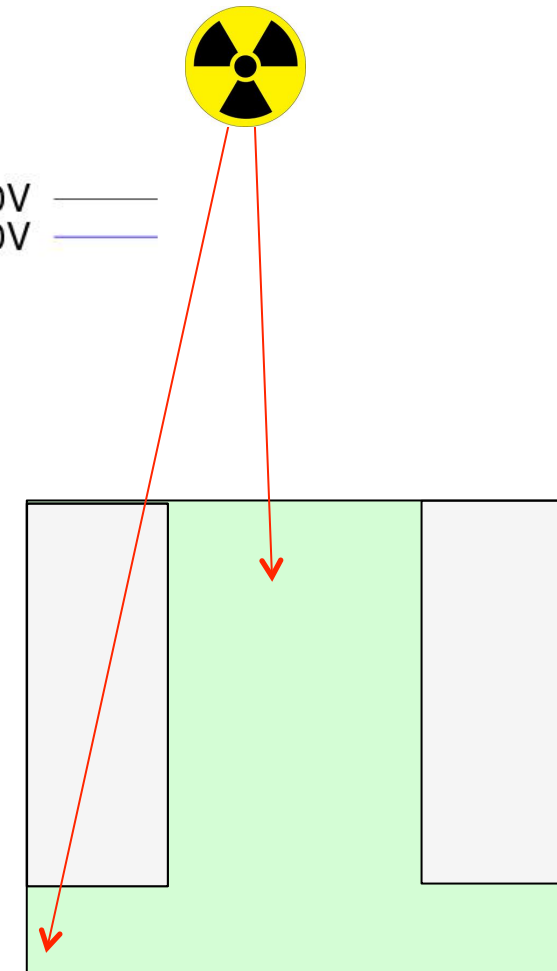
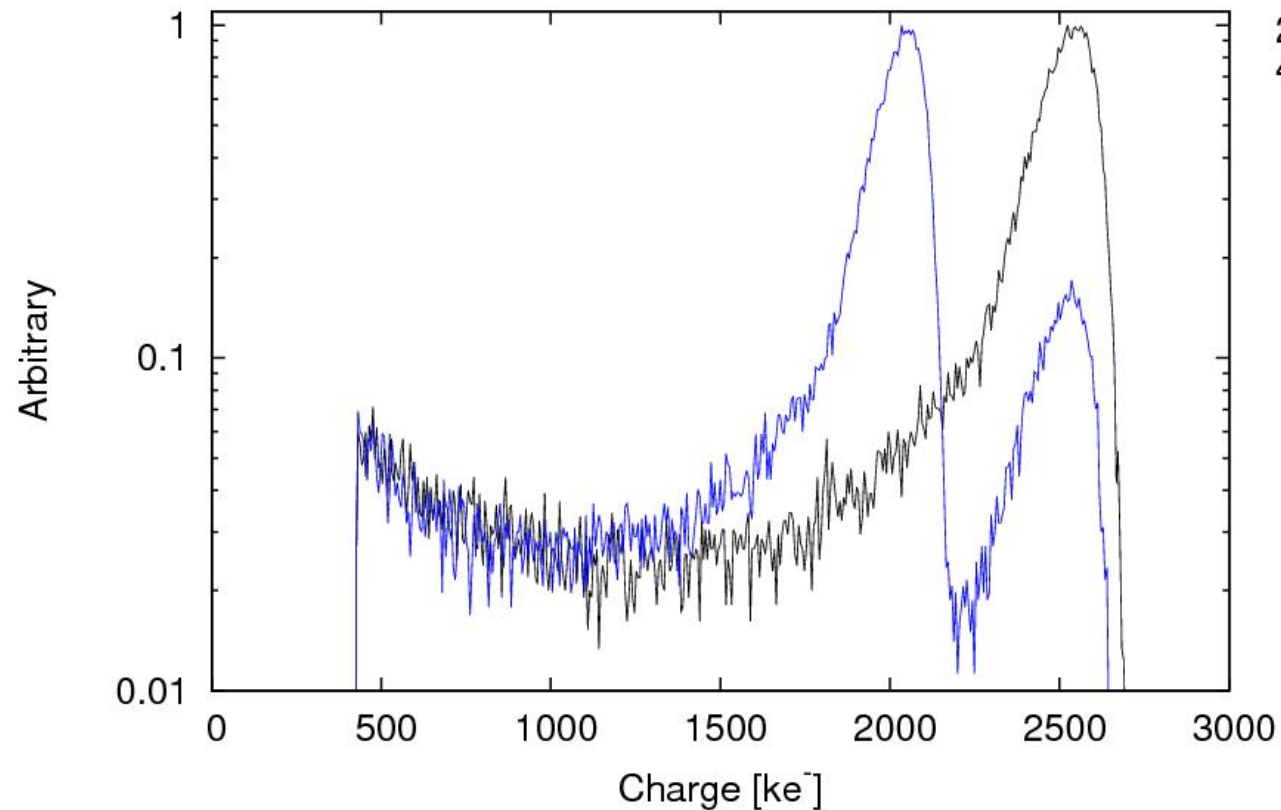


Breakdown most likely occurs  
at metal crossing p+ regions

# Lab. Test with alpha particles

$^{241}\text{Am}$   $\alpha$  source from cavity side

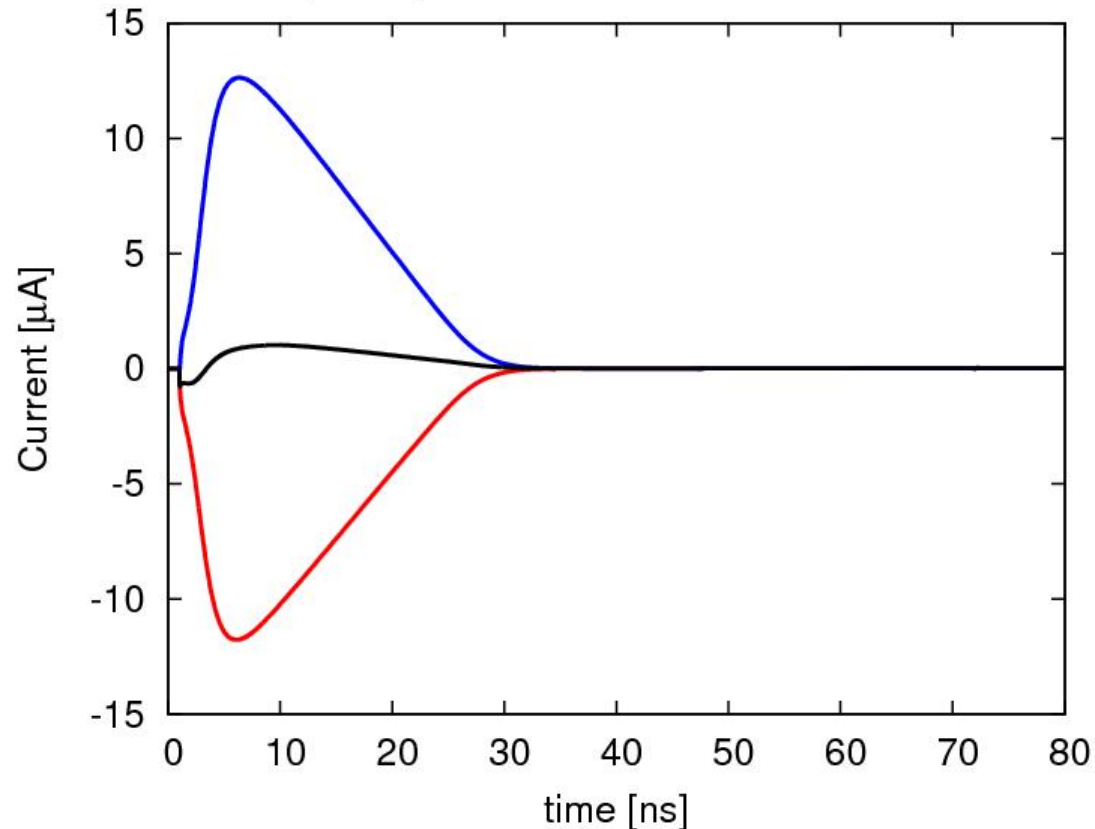
Read-out = Preamplifier + shaper (10 us) + MCA



Split of main energy peak at higher voltage ...

## TCAD simulation: $\alpha$ particle

### Alpha particle simulation 45 V

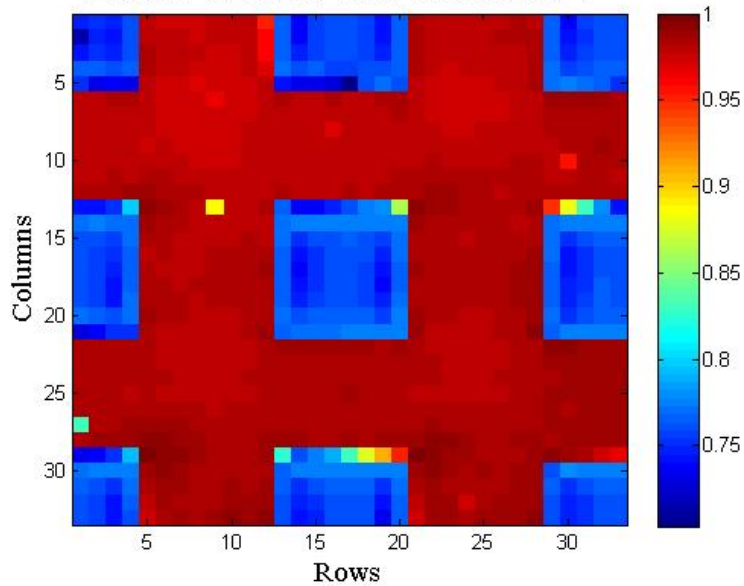


- Particle induces signals of opposite polarities on two adjacent electrodes
- In the diode configuration, signals of all electrodes are summed, causing strong compensation effects

**Problem to be solved with a full 3D sensor**

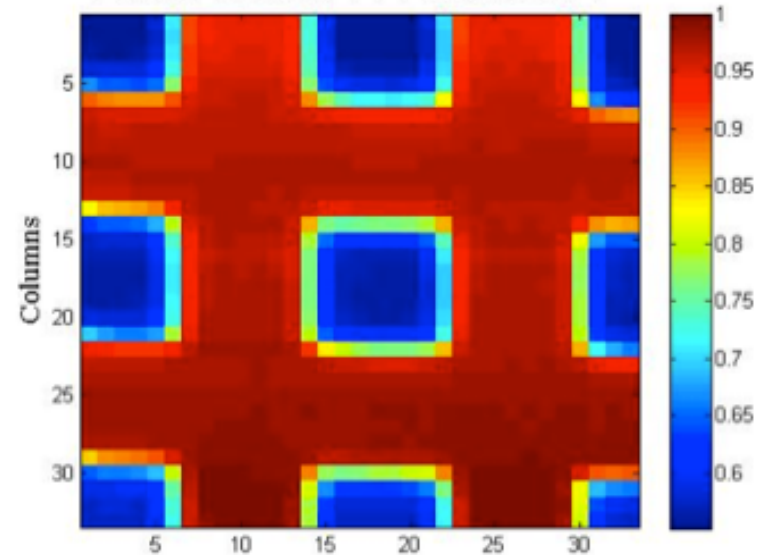
# Lab. Test with position resolved laser

Laser scan at 635 nm at 20V

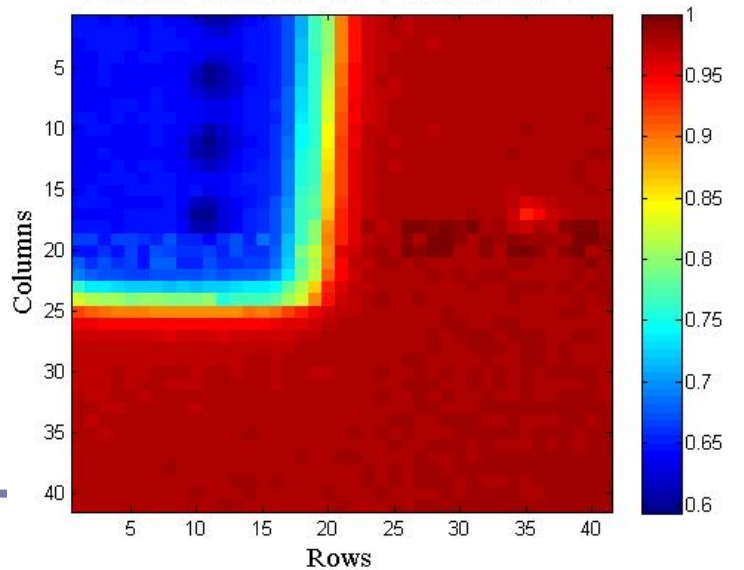


Good  
signal  
uniformity

Laser scan at 900 nm at 20V

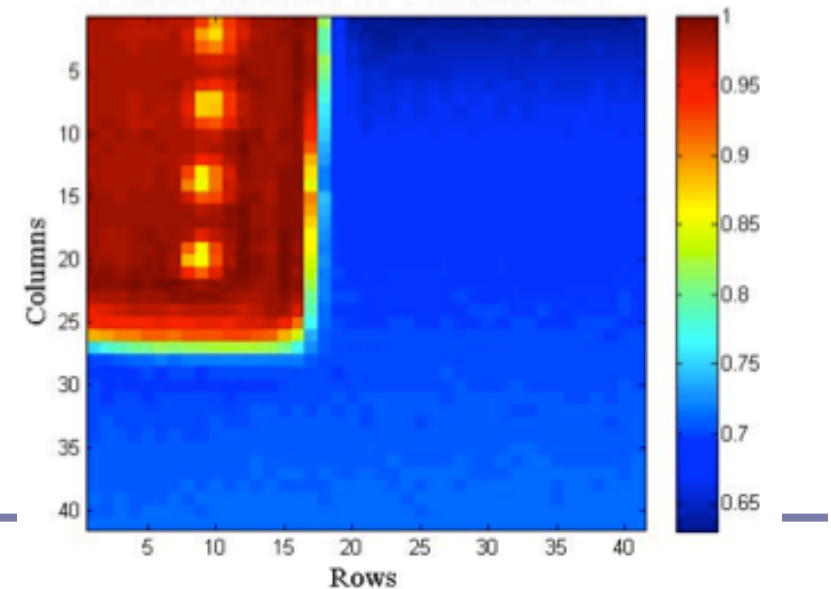


Laser scan at 850 nm at 20V



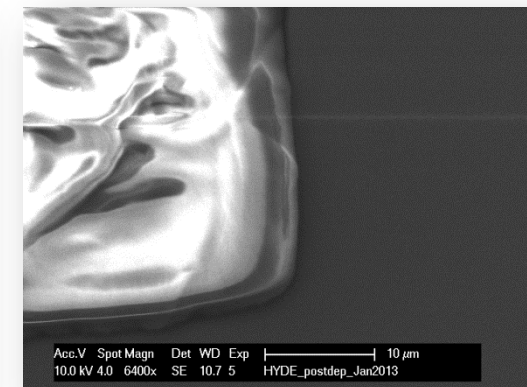
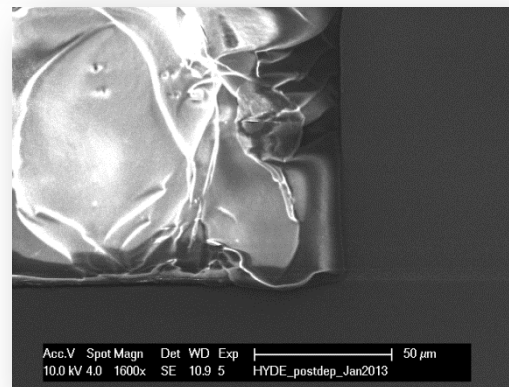
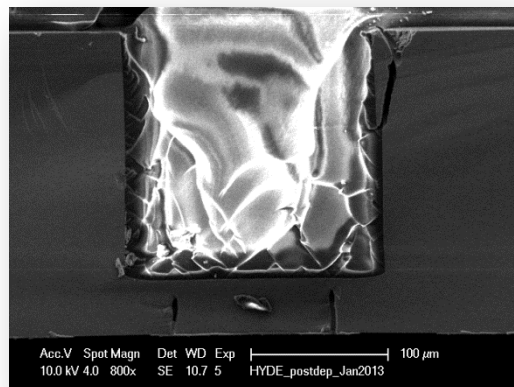
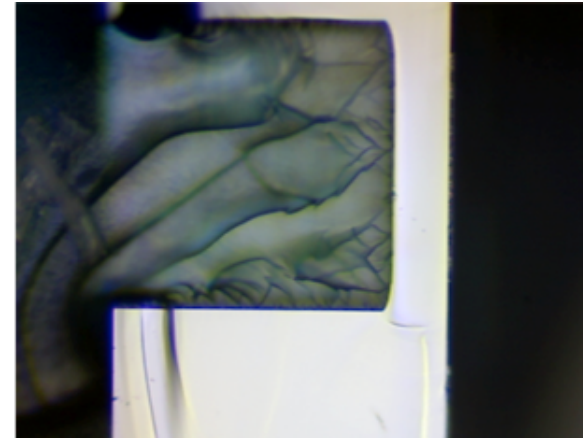
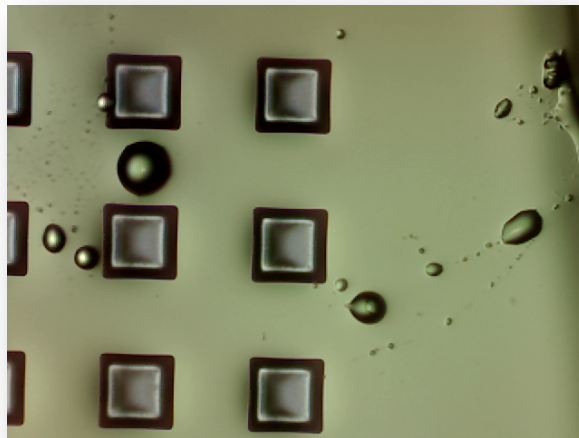
Signal  
amplitude  
"inversion"  
at larger  
voltages

Laser scan at 850 nm at 45V



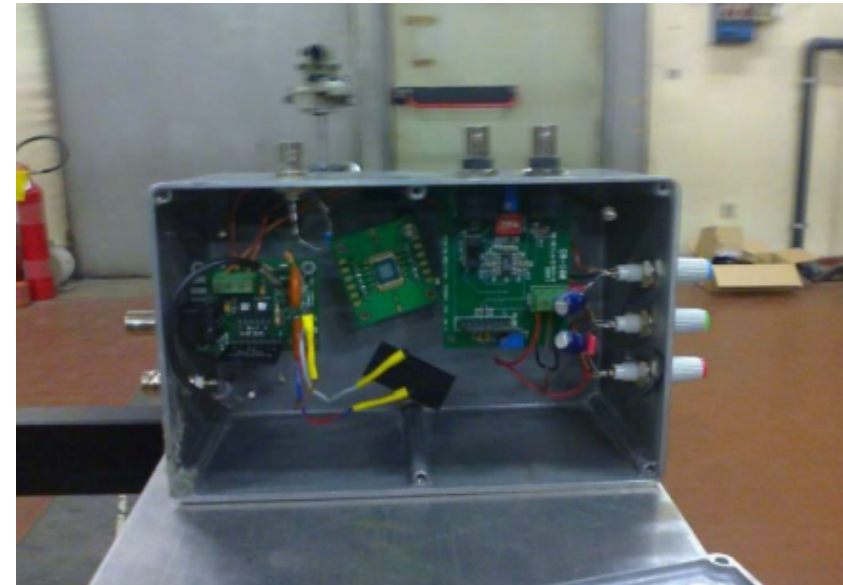
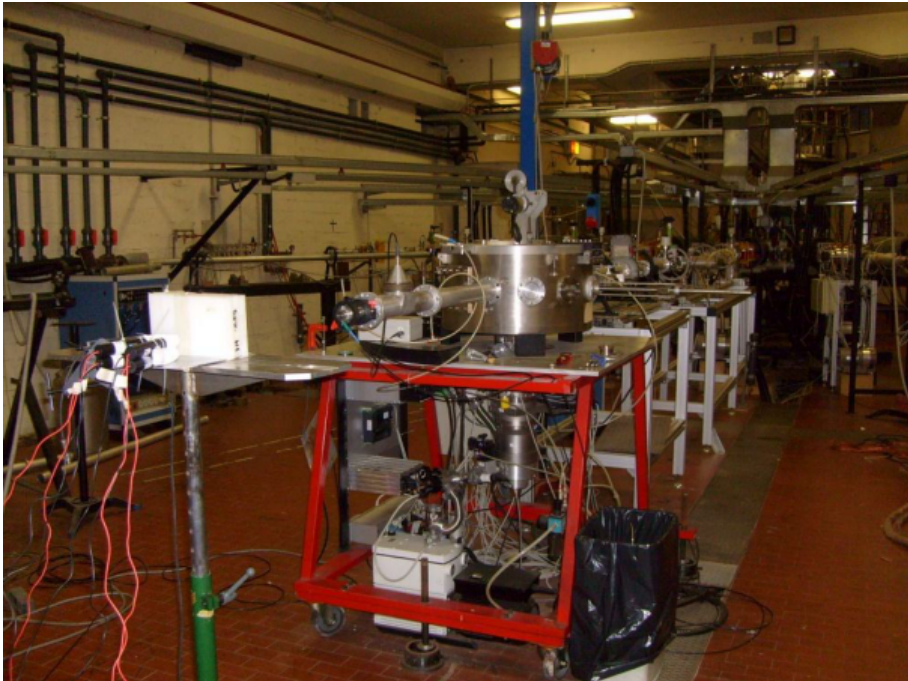
# Filling tests at LNL

Very good matching and adhesion of polysiloxane converter to silicon sensors





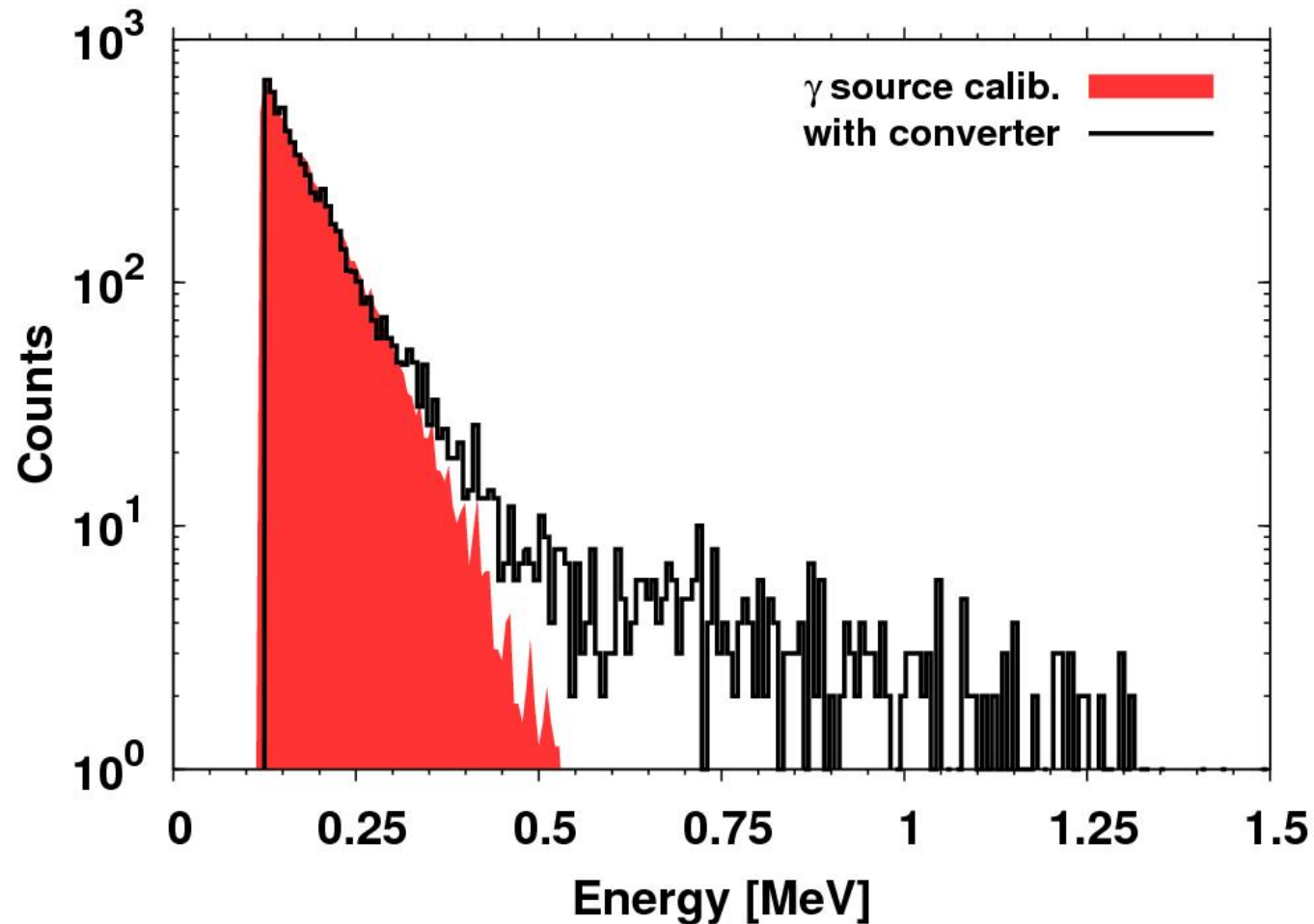
# Fast neutron detection setup



Pulsed proton beam on LiF target at CN 7 MeV accelerator of LNL

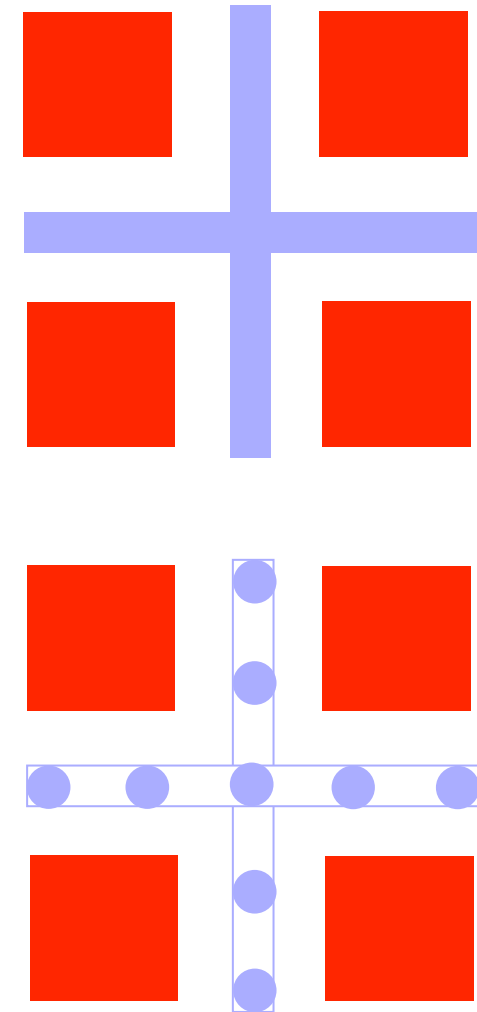
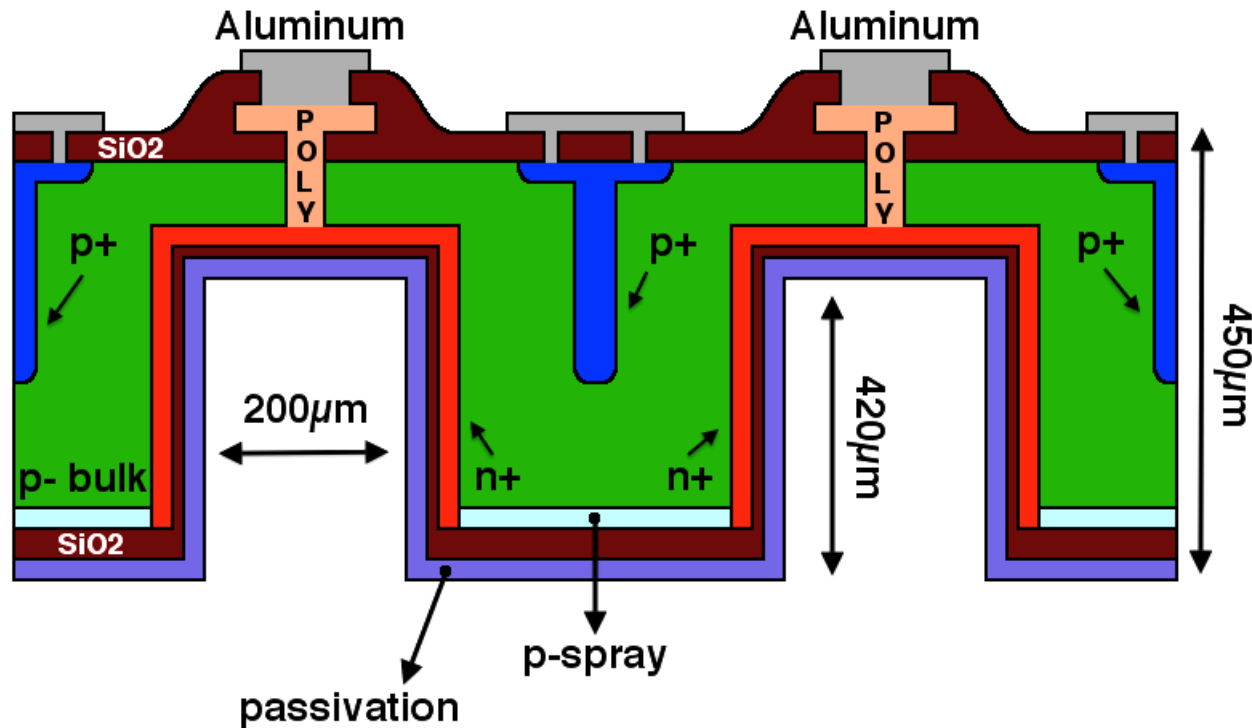
- 2 ns pulse width, 3 MHz repetition rate.
- Proton energy: 4.0 MeV. Main neutron peak: 2.3 MeV. ( ${}^7\text{Li}(p,n){}^7\text{Be}$ )

# Initial results



Encouraging results in spite of small device dimensions and low statistics. Further tests to come (next shift end of July) and efficiency analysis to be performed

# New full-3D structures

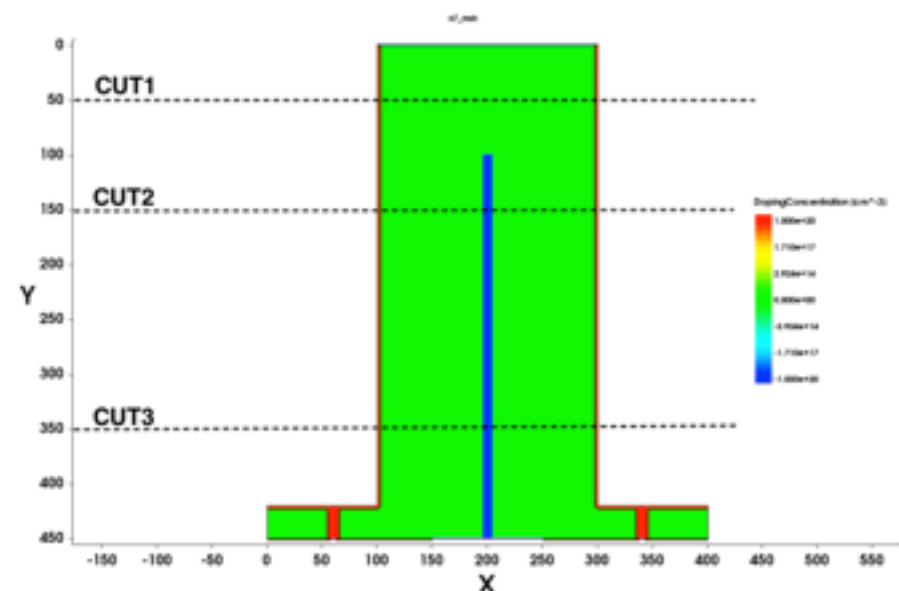
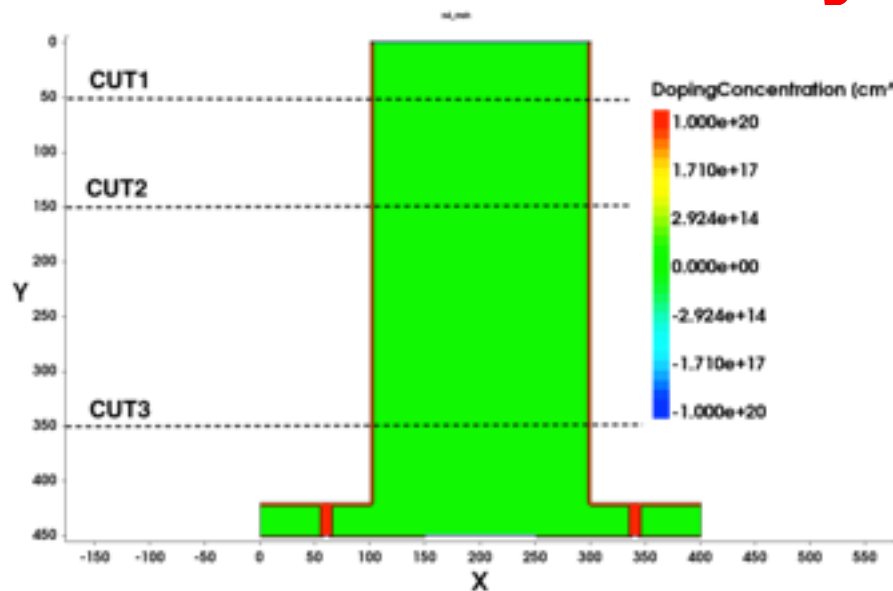


Full 3D sensors required to improve the performance

- Ohmic vertical electrodes to be added
- Trench vs Columns option

Note: new FBK line with 6" wafers: thicker sensors and thicker cavities

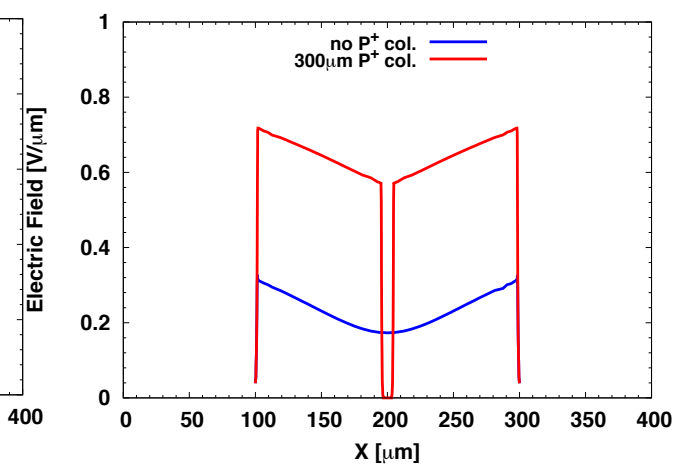
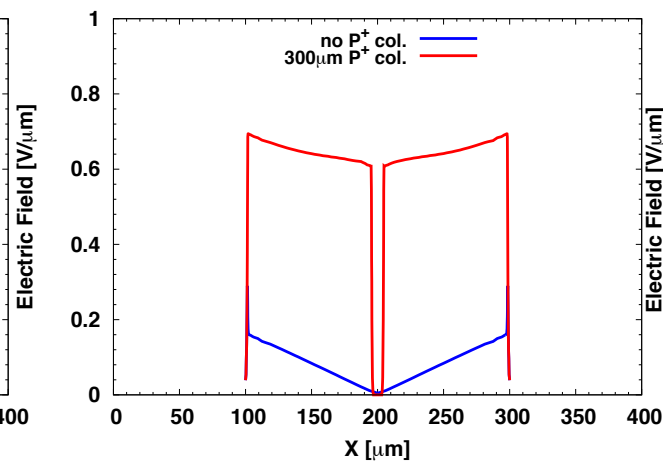
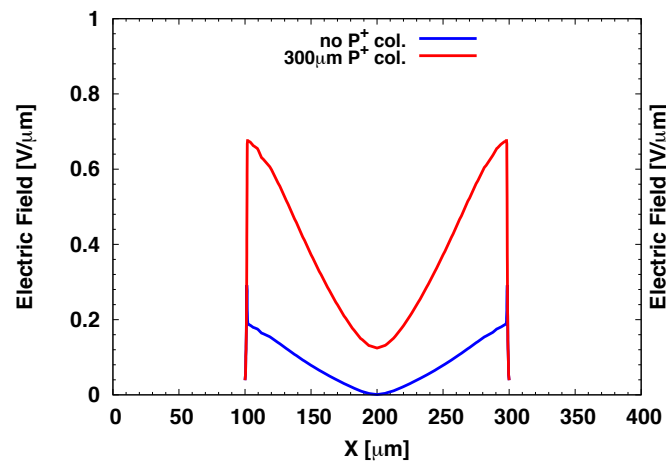
# Preliminary TCAD results



CUT1

CUT2

CUT3



# Workplan : end 2013 - 2014

- ➔ Complete lab. tests on 3D sensors from first batch
- ➔ Further tests with neutrons at LNL
  - ➔ More statistics required
  - ➔ Efficiency analysis
  - ➔ Coupling to an external photodetector
- ➔ TCAD simulation & design for second batch
- ➔ Fabrication of second batch at FBK
- ➔ Extensive characterization of sensors from second batch  
(also including radiation damage tests)

# Riassunto FTE 2014

<b>Persona</b>	<b>Ruolo</b>	<b>FTE</b>
Gian-Franco Dalla Betta (R)	PA	30%
Giovanni Verzellesi	PO	40%
David Macii	RU	50%
Lucio Pancheri	RTD	20%
Giorgio Fontana	TC. EP	30%
Roberto Mendicino	Dott.	50%
Nicola Persegona	L.M.	100%
Ennio Perillo	L.M.	100%
<b>Totale FTE per progetto</b>		<b>4,20</b>

**+ Contributo PD Gianmaria Collazuol**



# Riassunto richieste 2014

<b>Voce</b>	<b>Richiesta</b>
<b>Missioni:</b> Riunioni tecniche e attività di test presso LNL	1.0
<b>Consumabili:</b> Materiali x Laboratorio: (PCB, componenti elettronici, ... )	1.6
Fabbricazione 1 lotto sensori 3D @ FBK (prezzo convenzione @ 2200 Euro/lito eq.)	26.4
<b>Totale (k€)</b>	<b>29.0</b>

**Nessuna richiesta per officine**